

Silicon Switching Diode BAS16WT1G

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Symbol	Rating	Value	Unit
V _R	Continuous Reverse Voltage	100	V
I _R	Recurrent Peak Forward Current	200	mA
I _{FM(surge)}	Peak Forward Surge Current Pulse Width = 10 μs	500	mA
P _D	Total Power Dissipation, One Diode Loaded T _A = 25°C Derate above 25°C Mounted on a Ceramic Substrate (10 x 8 x 0.6 mm)	200 1.6	mW mW/°C
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient One Diode Loaded Mounted on a Ceramic Substrate (10 x 8 x 0.6 mm)	625	°C/W

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SC-70 CASE 419 STYLE 2



MARKING DIAGRAM



A6 = Specific Device Code

M = Date Code= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]	
BAS16WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel	
SBAS16WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel	

DISCONTINUED (Note 1)

NSVBAS16WT3G	SC-70	10,000 / Tape &	
	(Pb-Free)	Reel	

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
V _F	Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 50 \text{ mA})$ $(I_F = 50 \text{ mA})$	- - - -	715 866 1000 1250	mV
I _R	Reverse Current $(V_R = 100 \text{ V})$ $(V_R = 75 \text{ V}, T_J = 150^{\circ}\text{C})$ $(V_R = 25 \text{ V}, T_J = 150^{\circ}\text{C})$	- - -	1.0 50 30	μΑ
C _D	Capacitance $(V_R = 0, f = 1.0 \text{ MHz})$	-	2.0	pF
t _{rr}	Reverse Recovery Time (I _F = I _R = 10 mA, R _L = 50 Ω) (Figure 1)	-	6.0	ns
QS	Stored Charge (I _F = 10 mA to V_R = 6.0 V, R_L = 500 Ω) (Figure 2)	_	45	PC
V _{FR}	Forward Recovery Voltage ($I_F = 10 \text{ mA}, t_r = 20 \text{ ns}$) (Figure 3)	_	1.75	V

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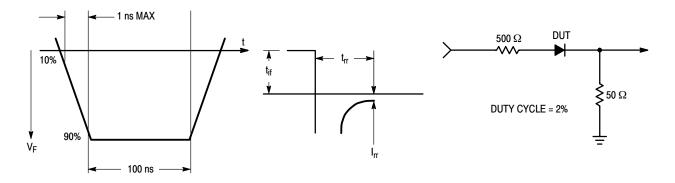


Figure 1. Reverse Recovery Time Equivalent Test Circuit

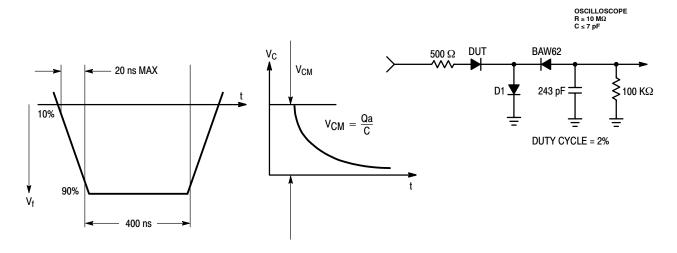


Figure 2. Stored Charge Equivalent Test Circuit

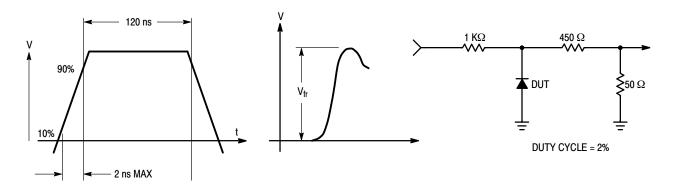


Figure 3. Forward Recovery Voltage Equivalent Test Circuit

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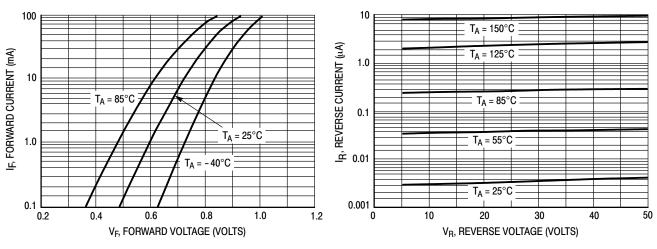


Figure 4. Forward Voltage

Figure 5. Leakage Current

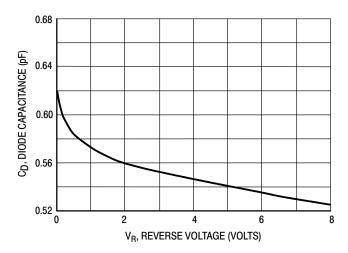


Figure 6. Capacitance







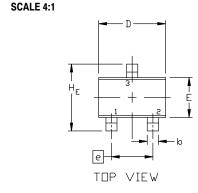
SC-70 (SOT-323) CASE 419 ISSUE R

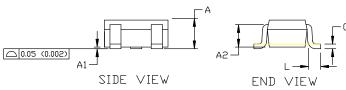
DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095





GENERIC MARKING DIAGRAM

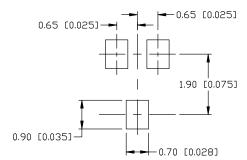


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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